



Features

- High power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management

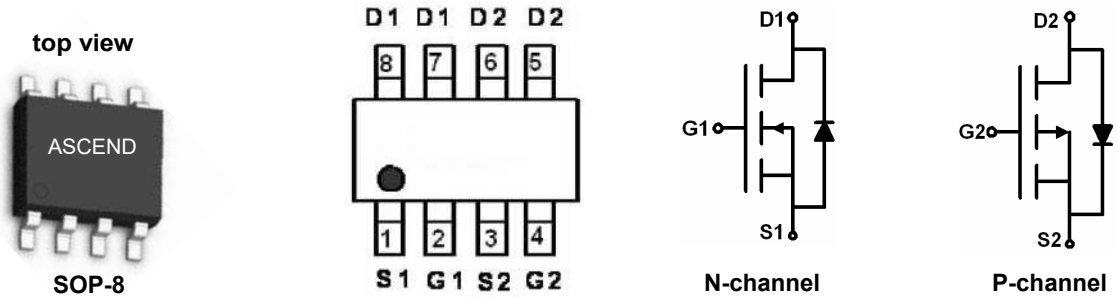
Product Summary

● N-Channel

BVDSS	RDSON.Typ@10V	ID
40V	28mΩ	7A

● P-Channel

BVDSS	RDSON.Typ@10V	ID
-40V	38mΩ	-6A



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	40	-40	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	7	-6	A
Pulsed Drain Current (Note 1)	I_{DM}	20	-20	A
Maximum Power Dissipation	P_D	2	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note2)	$R_{\theta JA}$	N-Ch	89	$^\circ\text{C/W}$
		P-Ch	90	

N-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1		2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5A	-	28	35	mΩ
		V _{GS} =4.5V, I _D =4A	-	36	45	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	620	-	PF
Output Capacitance	C _{oss}		-	110	-	PF
Reverse Transfer Capacitance	C _{rss}		-	70	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =3Ω V _{GS} =10V, R _{GEN} =3Ω	-	4.5	-	nS
Turn-on Rise Time	t _r		-	2.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	14.5	-	nS
Turn-Off Fall Time	t _f		-	3.5	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =5A, V _{GS} =10V	-	5.2	-	nC
Gate-Source Charge	Q _{gs}		-	0.85	-	nC
Gate-Drain Charge	Q _{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.3	V
Diode Forward Current (Note 2)	I _S		-	-	4	A

**.P.-CH. Electrical Characteristics (T_A=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-32V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1		-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-6A	-	38	46	mΩ
		V _{GS} =-4.5V, I _D =-3A	-	49	70	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.1A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	980	-	PF
Output Capacitance	C _{OSS}		-	120	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	95	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, R _L =3.6Ω V _{GS} =-10V, R _{GEN} =3Ω	-	9	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	28	-	nS
Turn-Off Fall Time	t _f		-	13.5	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4A, V _{GS} =-10V	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	3.1	-	nC
Gate-Drain Charge	Q _{gd}		-	3.	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1A	-	-	-1.3	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

N- Channel Typical Electrical and Thermal Characteristics (Curves)

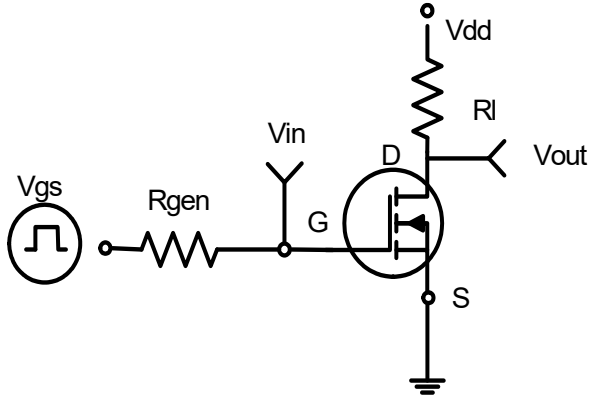


Figure 1: Switching Test Circuit

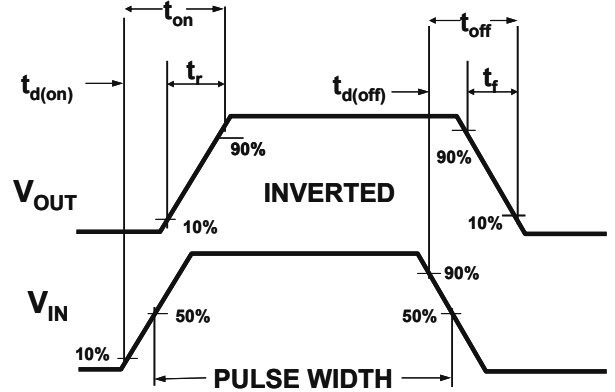


Figure 2: Switching Waveforms

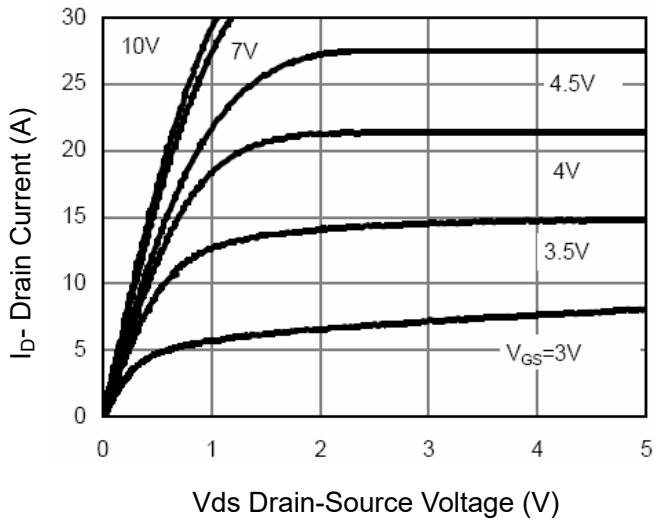


Figure 3 Output Characteristics

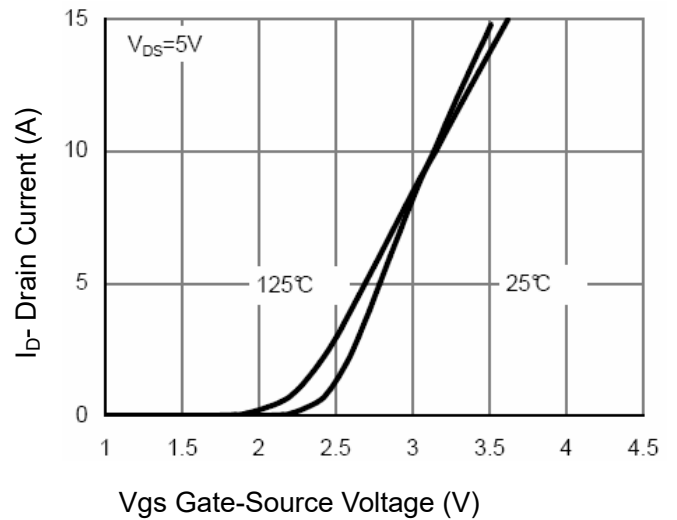


Figure 4 Transfer Characteristics

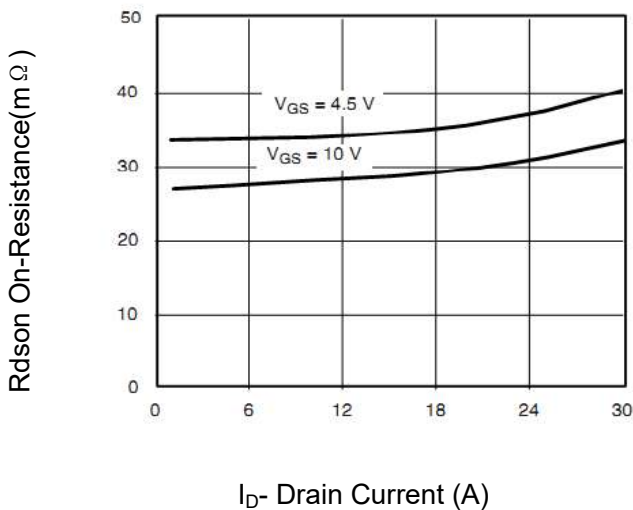


Figure 5 Drain-Source On-Resistance

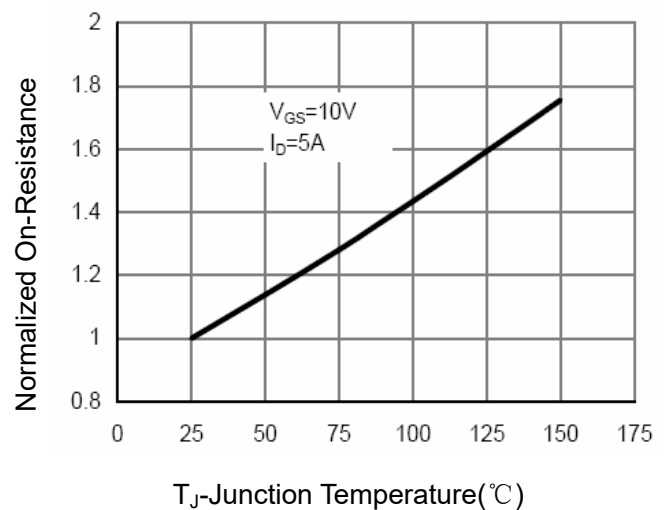
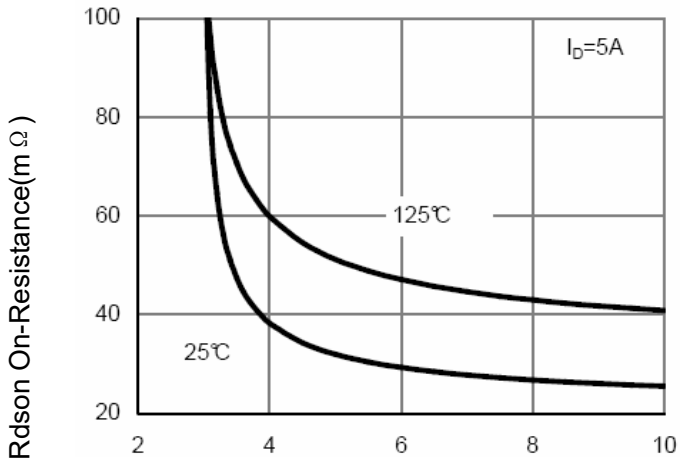
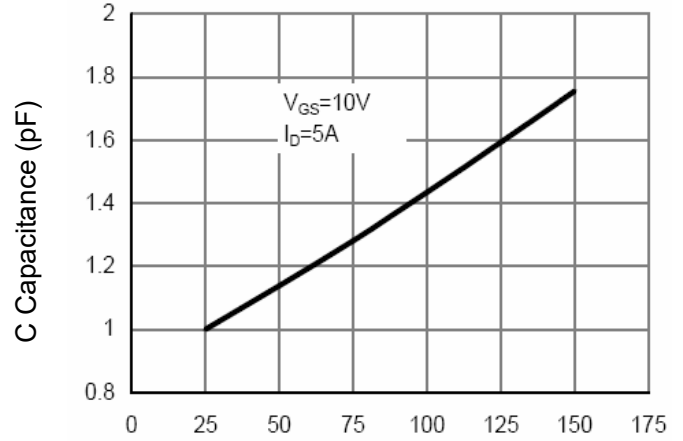


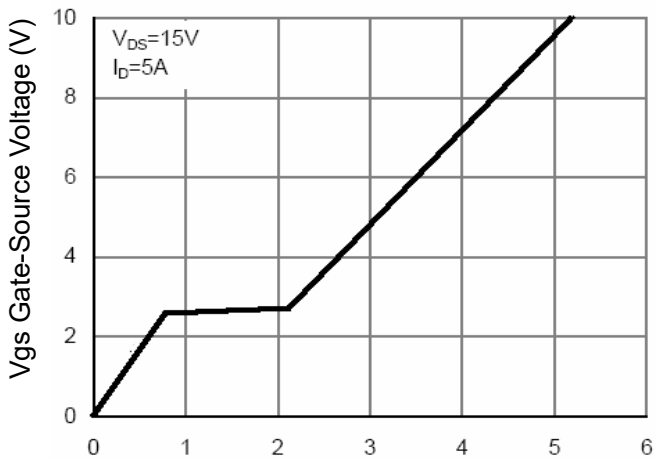
Figure 6 Drain-Source On-Resistance



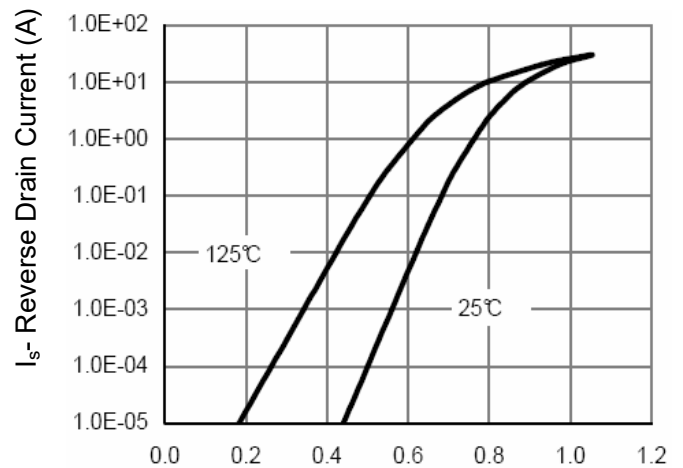
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



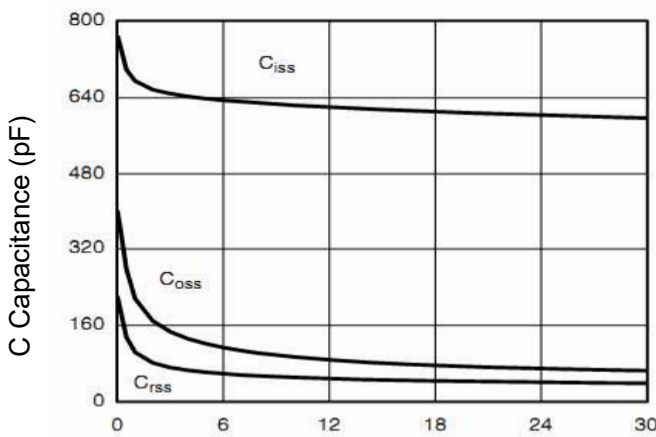
T_J-Junction Temperature(°C)
Figure 8 Drain-Source On-Resistance



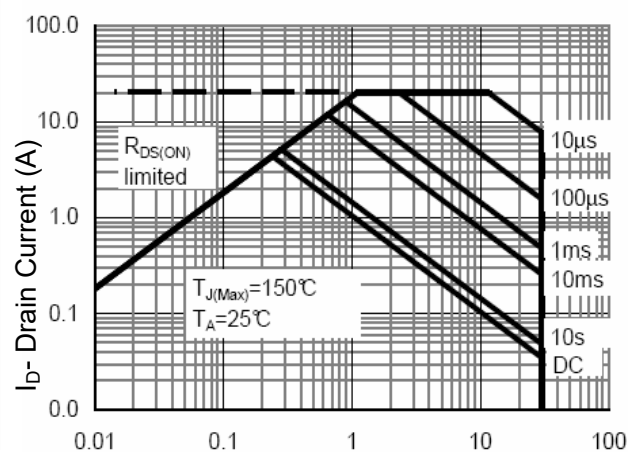
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

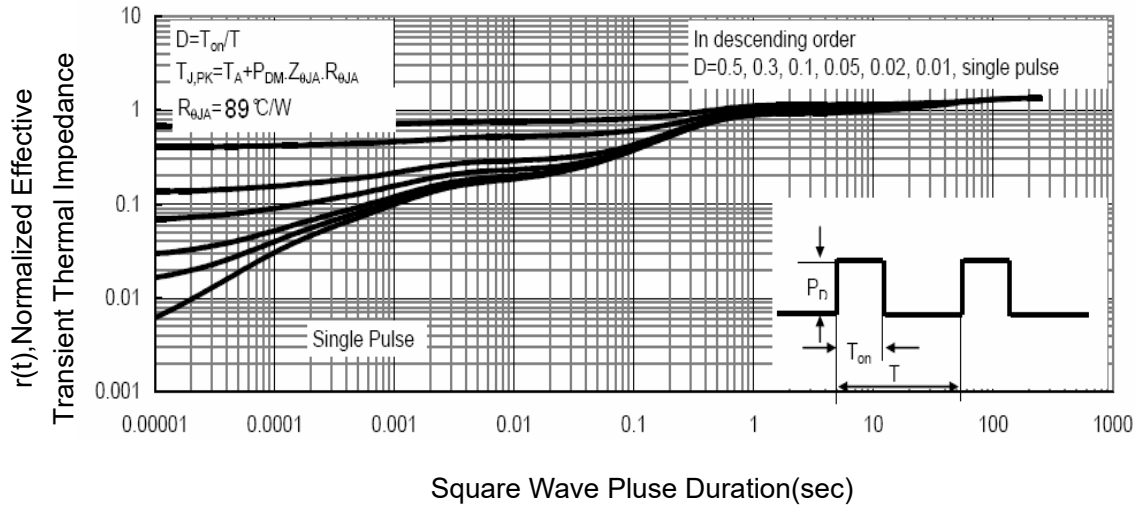


Figure 13 Normalized Maximum Transient Thermal Impedance

P-Channel Typical Electrical and Thermal Characteristics

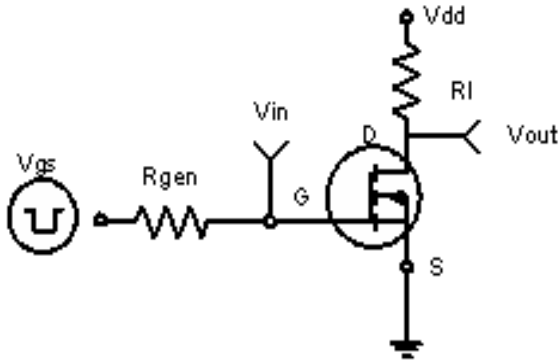


Figure 1: Switching Test Circuit

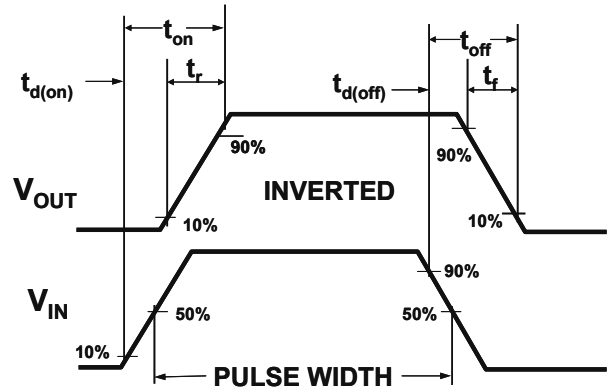


Figure 2: Switching Waveforms

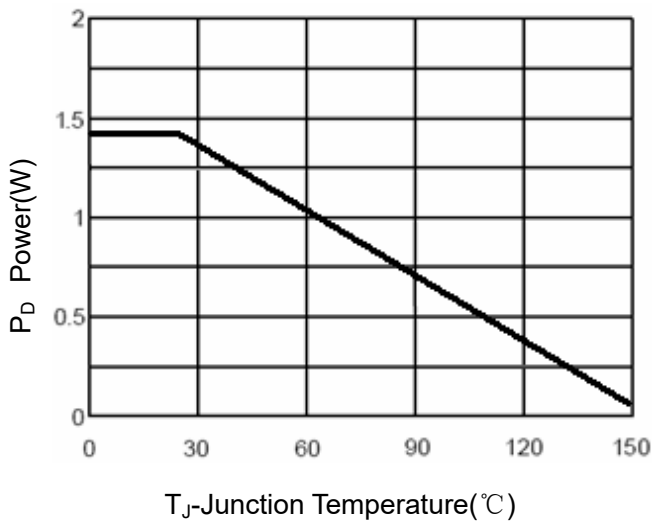


Figure 3 Power Dissipation

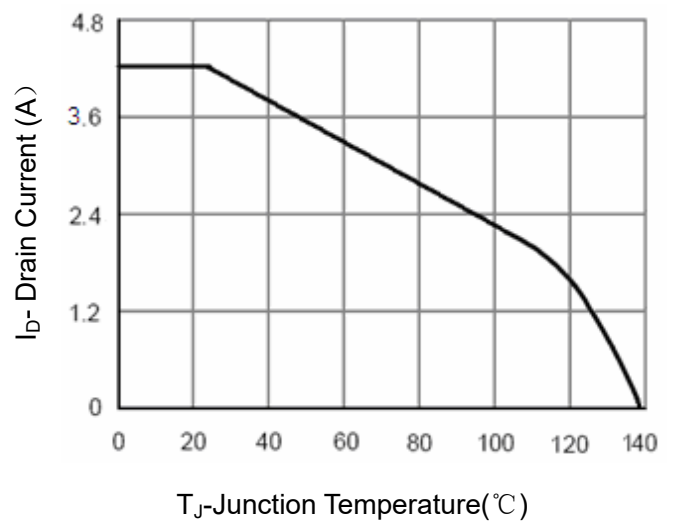


Figure 4 Drain Current

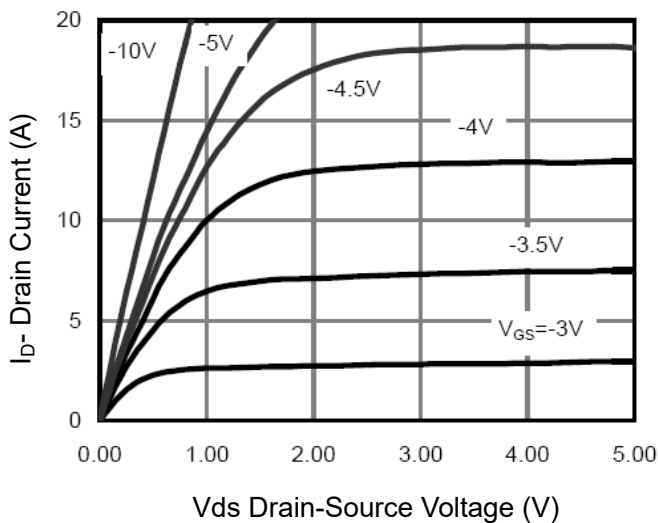


Figure 5 Output CHARACTERISTICS

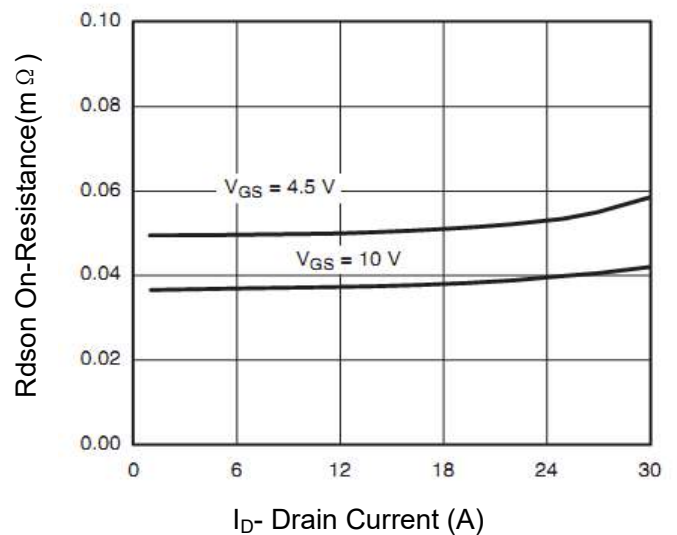


Figure 6 Drain-Source On-Resistance

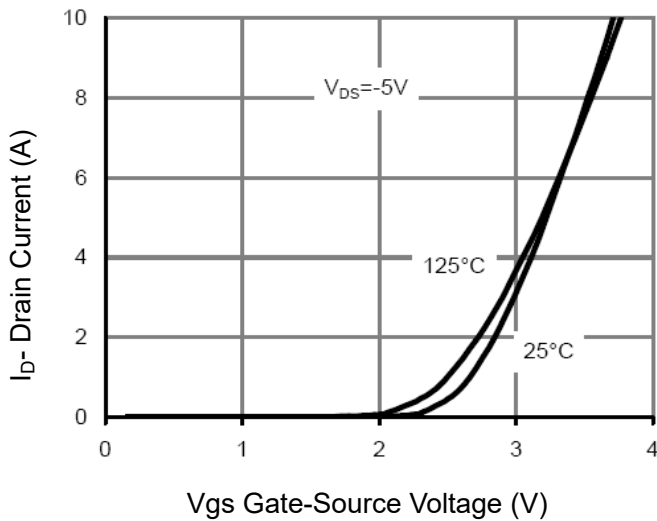


Figure 7 Transfer Characteristics

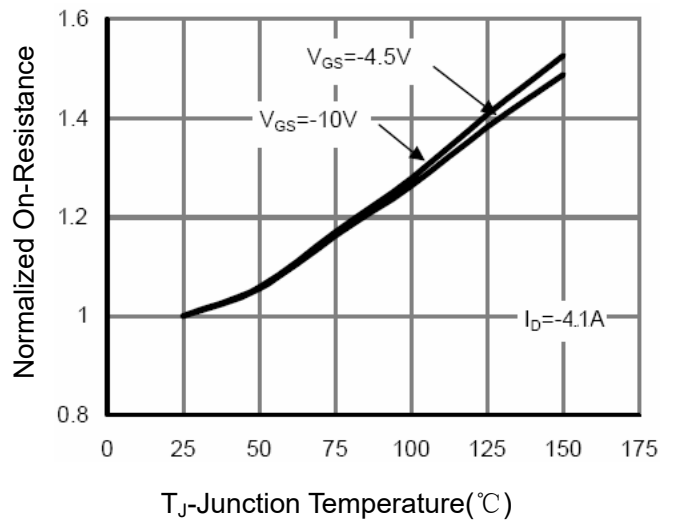


Figure 8 Drain-Source On-Resistance

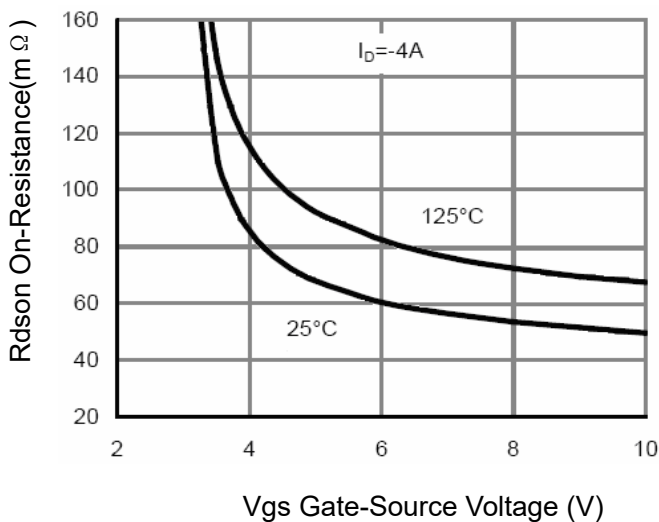


Figure 9 Rdson vs Vgs

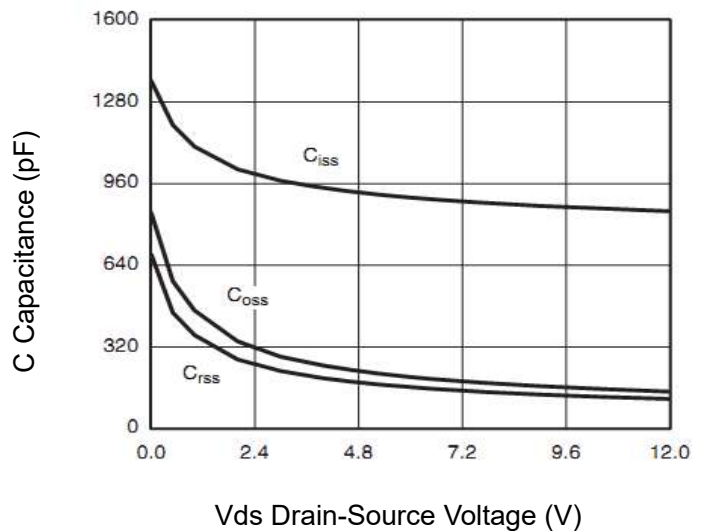


Figure 10 Capacitance vs Vds

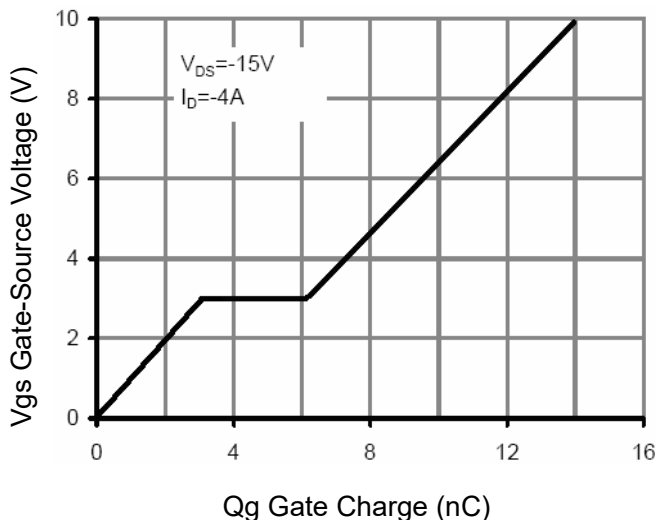


Figure 11 Gate Charge

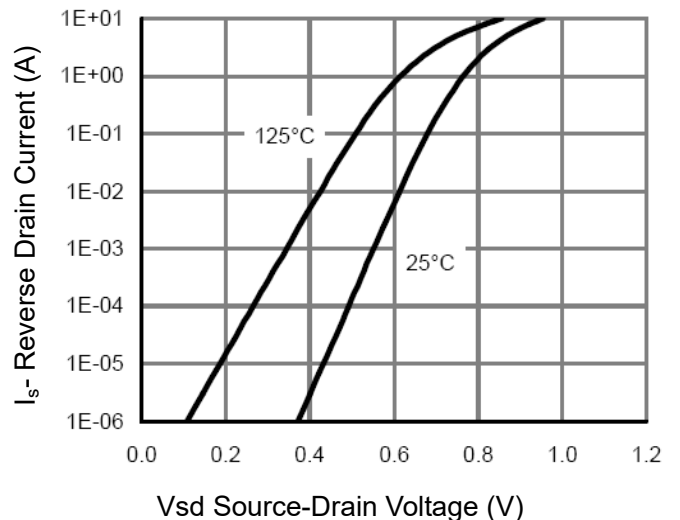


Figure 12 Source- Drain Diode Forward

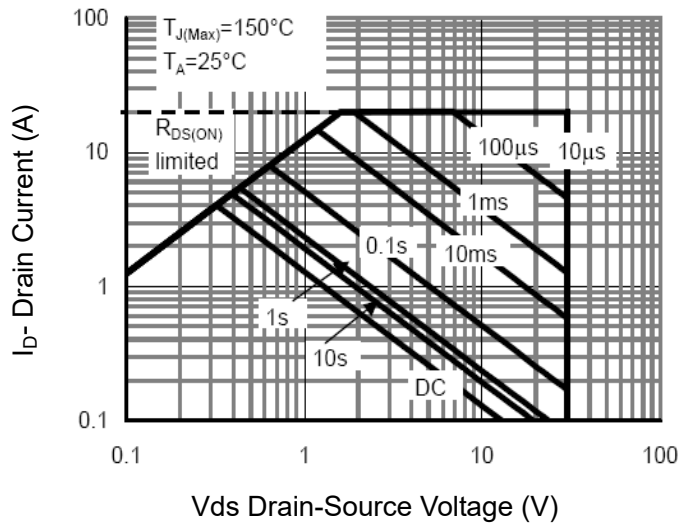


Figure 13 Safe Operation Area

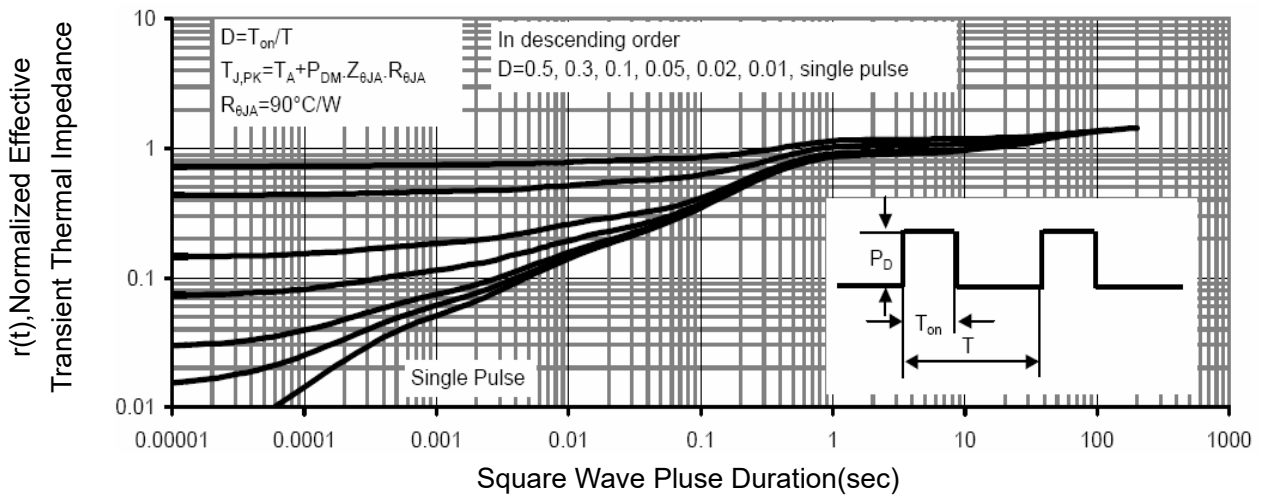
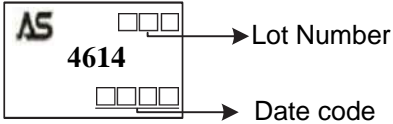


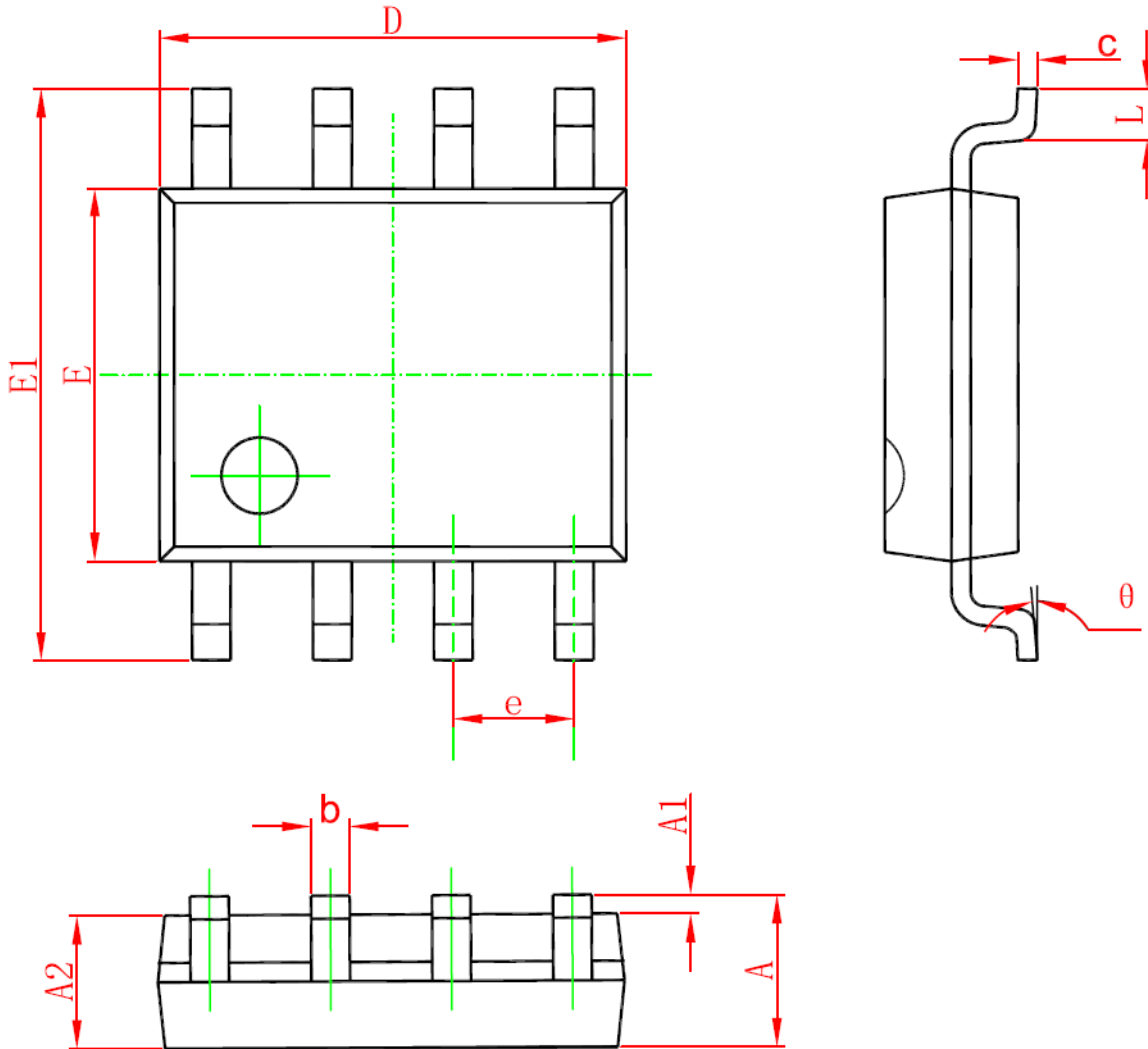
Figure 14 Normalized Maximum Transient Thermal Impedance

Ordering and Marking Information

Ordering Device No.	Marking	Package	Packing	Quantity
ASDM4614S-R	4614	SOP-8	Tape&Reel	4000/Reel

PACKAGE	MARKING
SOP-8	 <p>The diagram shows a rectangular marking area on an SOP-8 package. It contains the letters 'AS' in the top left, the number '4614' in the center, and two sets of three small squares. An arrow points from the top set of squares to the text 'Lot Number', and another arrow points from the bottom set of squares to the text 'Date code'.</p>

SOP-8 PACKAGE IN FORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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[C3M0021120D](#) [DMN6022SSD-13](#)